

DUAL P-CHANNEL ENHANCEMENT MODE MOSFET
Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ max}$	I_D $T_A = +25^\circ\text{C}$
-20V	38m Ω @ $V_{GS} = -10\text{V}$	-5.7A
	43m Ω @ $V_{GS} = -4.5\text{V}$	-5.4A
	75m Ω @ $V_{GS} = -2.5\text{V}$	-4.1A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- Battery Pack
- Load Switch

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

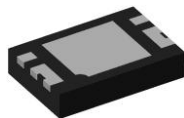
Mechanical Data

- Case: U-DFN2030-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.012 grams (Approximate)

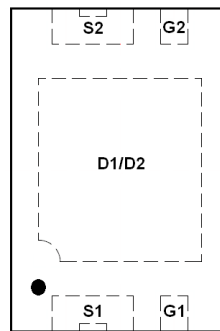


ESD PROTECTED

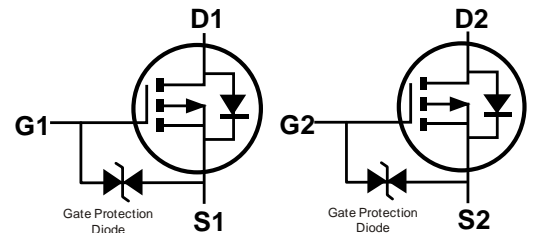
U-DFN2030-6



Bottom View



Top View

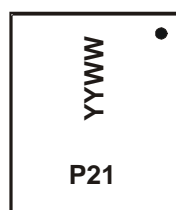


Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2100UFU-7	U-DFN2030-6	3000 / Tape & Reel
DMP2100UFU-13	U-DFN2030-6	10000 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information


P21 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Digit of Year (ex: 14 for 2014)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±10	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	I _D	-5.7 -4.4	A
Maximum Continuous Body Diodes Forward Current (Note 6)			I _S	-2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-30	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	-15	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	12	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	138	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	66	°C/W
Thermal Resistance, Junction to Case		R _{θJC}	9.6	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	µA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.3	—	-1.4	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	25	38	mΩ	V _{GS} = -10V, I _D = -3.5A
		—	29	43		V _{GS} = -4.5V, I _D = -3A
		—	37	75		V _{GS} = -2.5V, I _D = -1A
		—	47	—		V _{GS} = -1.8V, I _D = -0.5A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -2.9A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	906	—	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{OSS}	—	103	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	29	—	pF	
Gate Resistance	R _g	—	259	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	10.3	—	nC	V _{DS} = -10V, I _D = -4A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	21.4	—	nC	
Gate-Source Charge	Q _{GS}	—	1.6	—	nC	
Gate-Drain Charge	Q _{GD}	—	2.3	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	70	—	ns	V _{DS} = -10V, V _{GS} = -4.5V, R _L = 2.5Ω, R _G = 3.0Ω
Turn-On Rise Time	t _r	—	144	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	626	—	ns	
Turn-Off Fall Time	t _f	—	396	—	ns	
Body Diode Reverse Recovery Time	t _{RR}	—	279	—	ns	I _F = -3.5A, di/dt = -100A/µs
Body Diode Reverse Recovery Charge	Q _{rr}	—	466	—	nC	I _F = -3.5A, di/dt = -100A/µs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

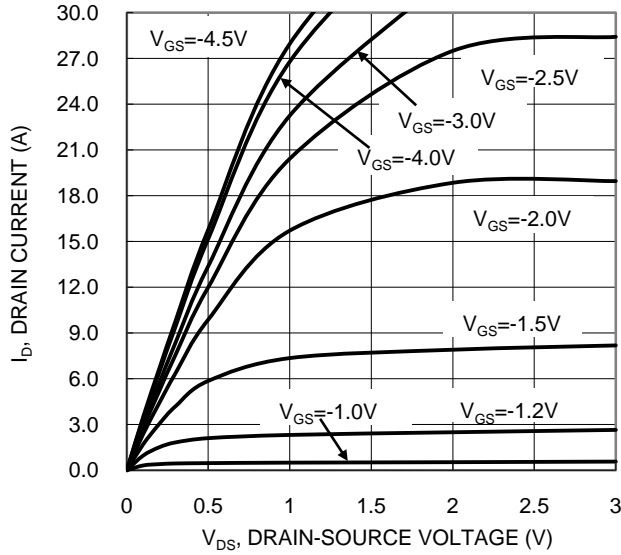


Figure 1. Typical Output Characteristic

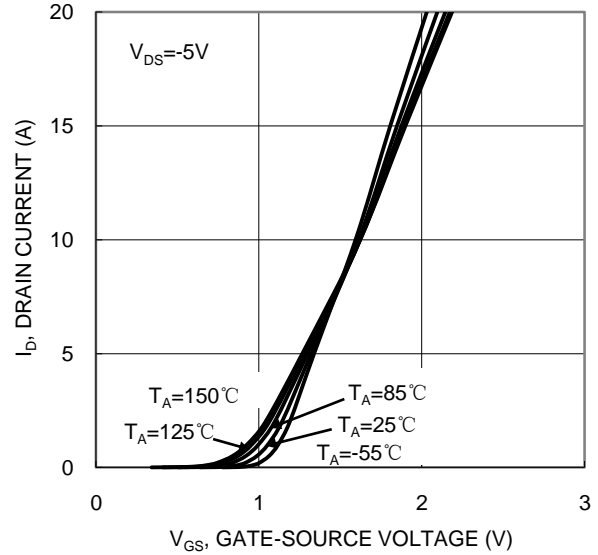


Figure 2. Typical Transfer Characteristic

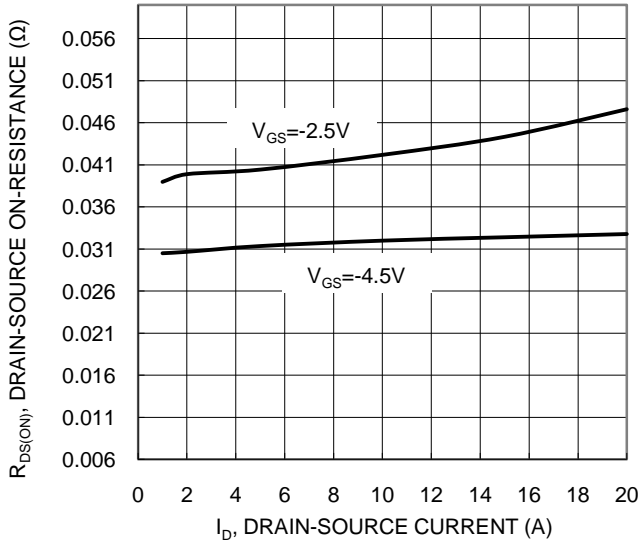


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

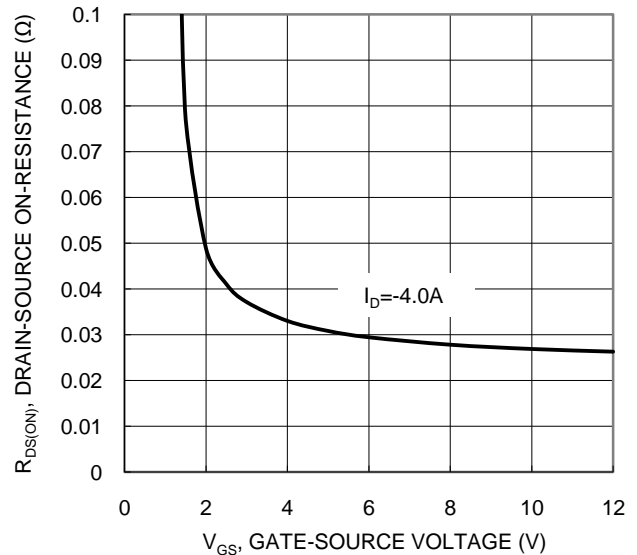


Figure 4. Typical Transfer Characteristic

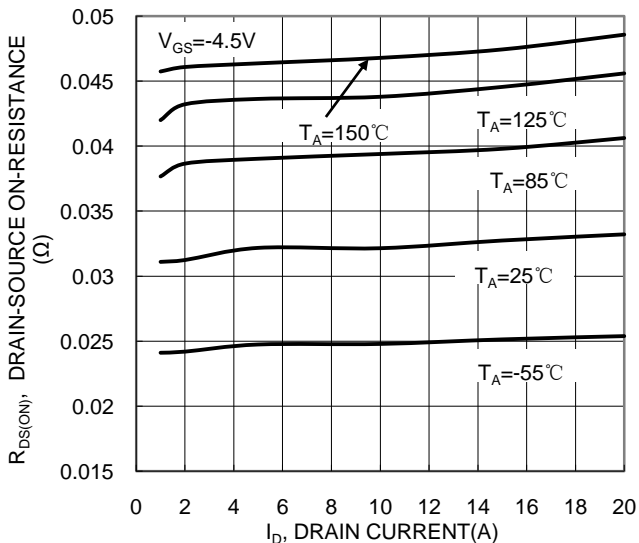


Figure 5. Typical On-Resistance vs Drain Current and Temperature

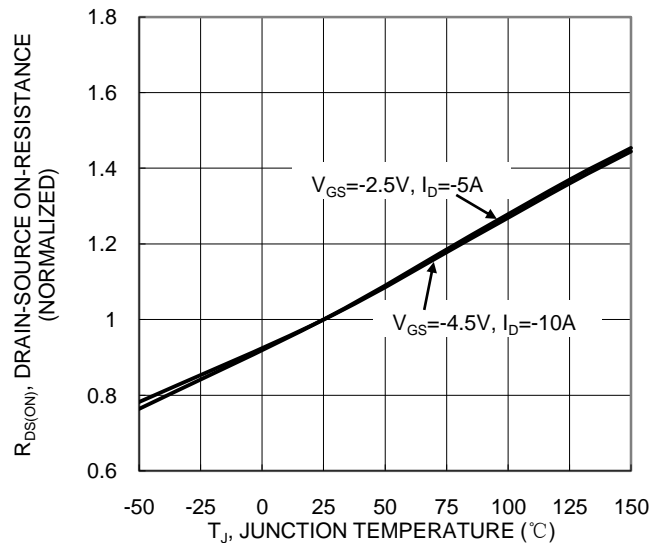
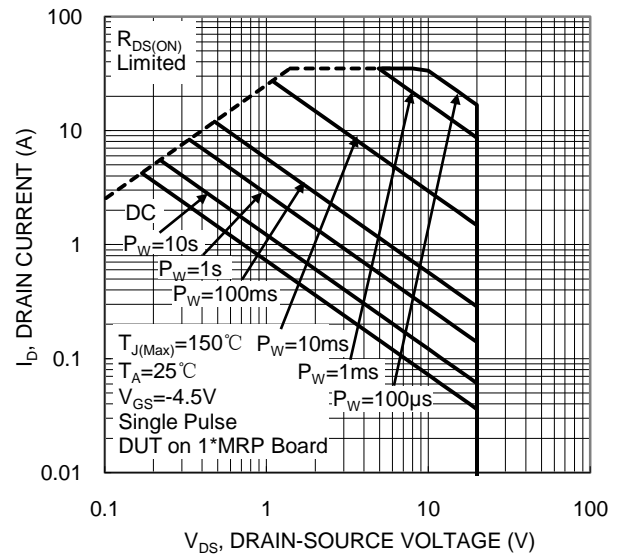
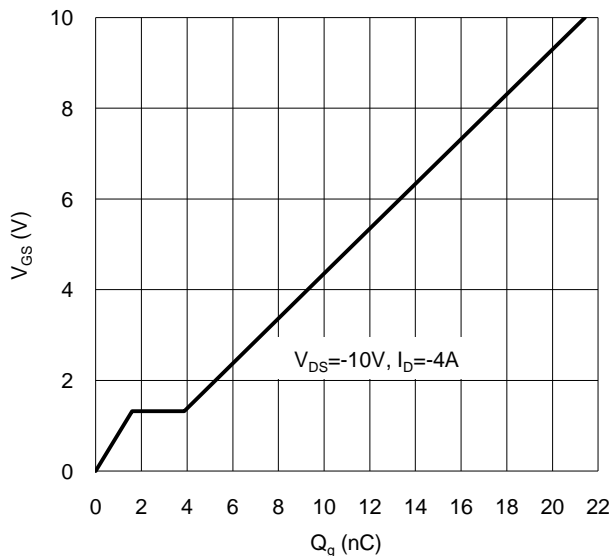
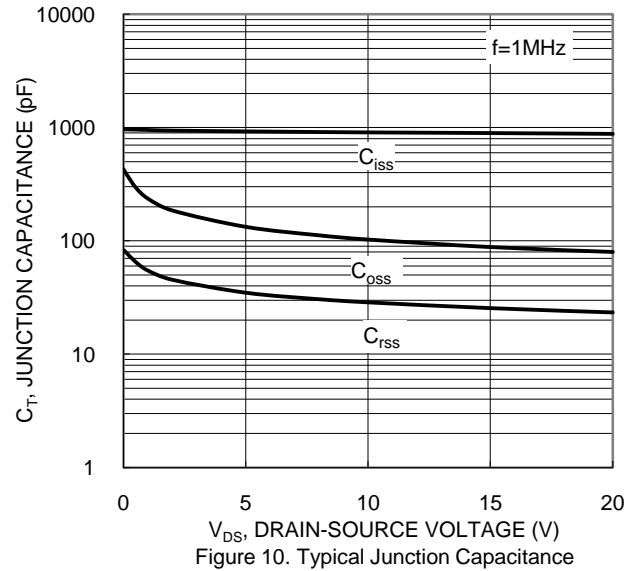
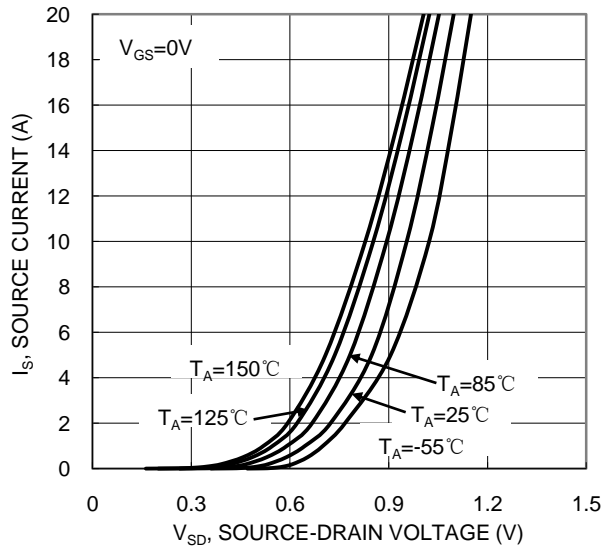
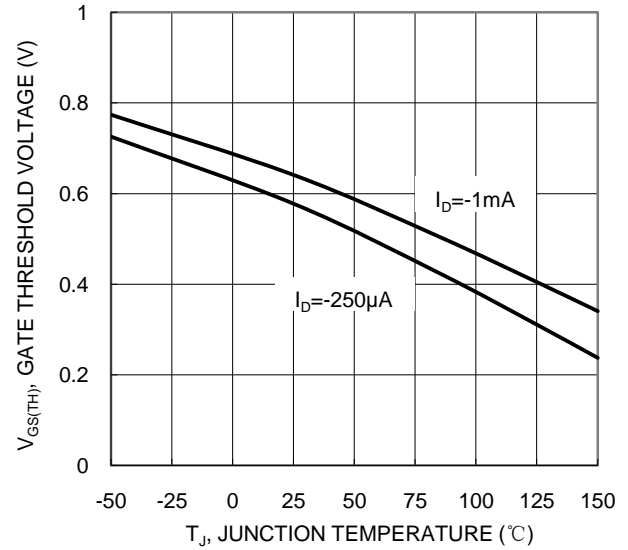
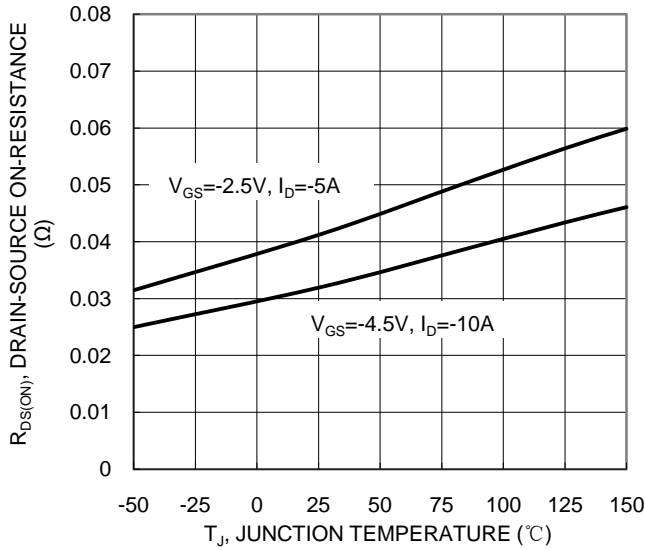


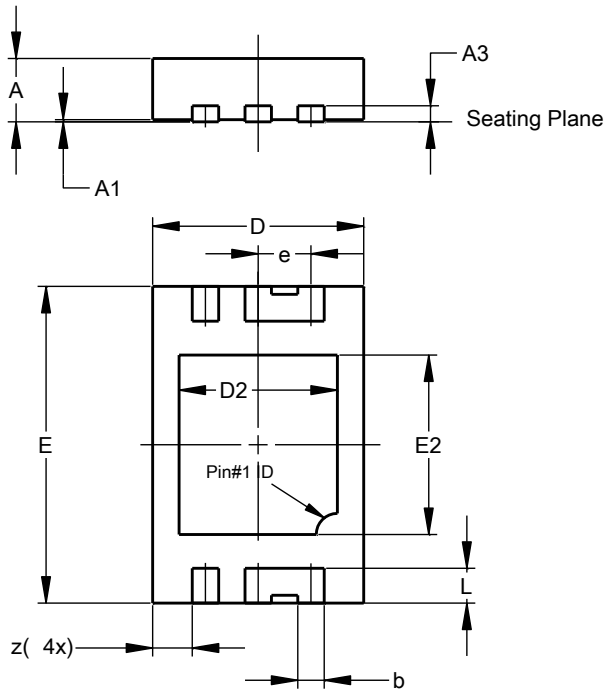
Figure 6. On-Resistance Variation with Temperature



DMP2100UFU
Document number: DS37946 Rev. 1 - 2

Package Outline Dimensions

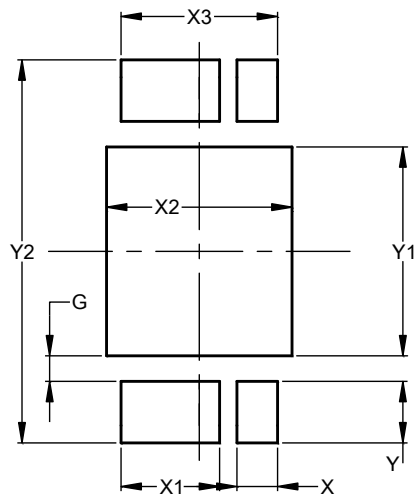
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



U-DFN2030-6 (Type B)			
Dim	Min	Max	Typ
A	0.55	0.65	0.60
A1	0.00	0.05	0.02
A3	--	--	0.15
b	0.20	0.30	0.25
D	1.95	2.05	2.00
D2	1.40	1.60	1.50
E	2.95	3.05	3.00
E2	1.65	1.75	1.70
e	--	--	0.50
L	0.28	0.38	0.33
z	--	--	0.375
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
G	0.220
X	0.350
X1	0.850
X2	1.600
X3	1.350
Y	0.530
Y1	1.800
Y2	3.300

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